

SEMISTACK

Antiparallel thyristors for softstart

SKKQ 160

Features

- Compact design
- · Thyristor with amplifying gate
- Pressure contact technology

Typical Applications

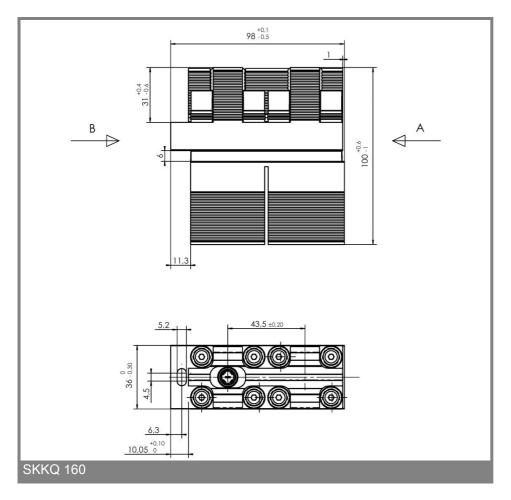
Soft Starters

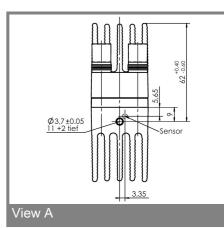
 T_{vjmax} up to 150°C is allowable for overload conditions, max. time period for the overload condition is 25s.

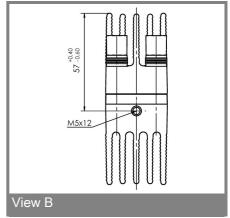
| Absolute Maximum Ratings | | | | | | | |
|--------------------------|--|------------------------|-------|--|--|--|--|
| Symbol | Conditions | Values | Units | | | | |
| I _{overload} | W1C; sin. 180°; 20 sec.; T _{vjmax.} = 150 °C; T _{vjstart} = 40°C | 560 | Α | | | | |
| I _{TSM} | $T_{vj} = 25^{\circ}C; 10 \text{ ms}$ | 5700 | Α | | | | |
| | $T_{vi} = 125^{\circ}C; 10 \text{ ms}$ | 5200 | Α | | | | |
| I²t | T _{vj} = 25°C; 8,3 10 ms | 162000 | A²s | | | | |
| | T _{vj} = 125°C; 8,3 10 ms | 135000 | A²s | | | | |
| SKKQ 160/14 | | | | | | | |
| V_{RSM} | | 1500 | V | | | | |
| V_{RRM}, V_{DRM} | | 1400 | V | | | | |
| SKKQ 160/18 | | | | | | | |
| V_{RSM} | | 1900 | V | | | | |
| V_{RRM}, V_{DRM} | | 1800 | V | | | | |
| T _{vj} | | -40 +125 ¹⁾ | °C | | | | |
| T _{stg} | | -40 + 125 | °C | | | | |

| Characteristics | | | | | | |
|-----------------------|--|------|---------|-------|-------|--|
| Symbol | Conditions | min. | typ. | max. | Units | |
| V_T | $T_{vi} = 25^{\circ}C; I_{T} = 1000 A$ | | | 1,9 | V | |
| $V_{T(TO)}$ | $T_{vj} = 125^{\circ}C$ | | | 0,9 | V | |
| r _T | $T_{vj} = 125^{\circ}C$ | | | 0,9 | mΩ | |
| $I_{DD};I_{RD}$ | T_{vj} = 125°C; $V_{RD} = V_{RRM}$; per module | | | 60 | mA | |
| t _{gd} | $T_{vj} = 25^{\circ}C; I_{G} = 1A; di_{G}/dt = 1A/\mu s$ | | 1 | | μs | |
| t _{gr} | $V_{D} = 0.67 * V_{DRM}$ | | 2 | | μs | |
| (dv/dt) _{cr} | T _{vi} = 125°C | | 1000 | | V/µs | |
| (di/dt) _{cr} | T _{vi} = 125°C; f = 50 60 Hz | | 125 | | A/µs | |
| t _q | T _{vi} = 125°C | | 150 | | μs | |
| I _H | $T_{vj} = 25^{\circ}C$ | | 150 | 400 | mA | |
| IL | $T_{vj} = 25^{\circ}C$; $R_G = 33 \Omega$ | | 300 | 1000 | mA | |
| V_{GT} | $T_{vi} = 25^{\circ}C; d.c.$ | 2 | | | V | |
| I_{GT} | $T_{v_i}^{\ \ } = 25^{\circ}C; d.c.$ | 150 | | | mA | |
| V_{GD} | T_{v_i} = 125°C; d.c. | | | 0,25 | V | |
| I_{GD} | $T_{vj} = 125^{\circ}C; d.c.$ | | | 10 | mA | |
| R _{th(j-s)} | cont.; per thyristor | | | 0,106 | K/W | |
| M _t | | | 5 ± 15% | | Nm | |
| m | | | 530 | | g | |
| Case | | | SKKQ160 | | | |









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